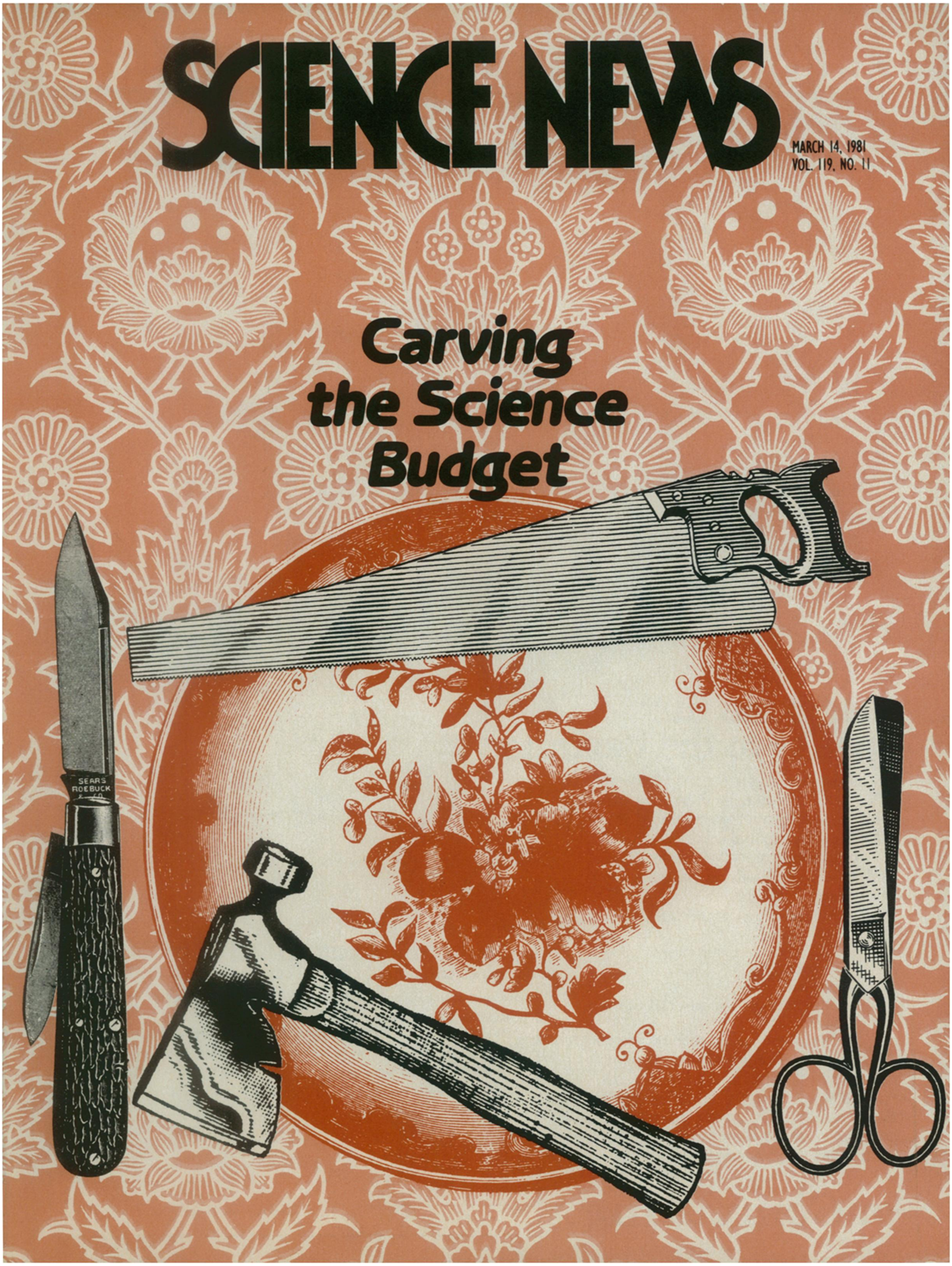
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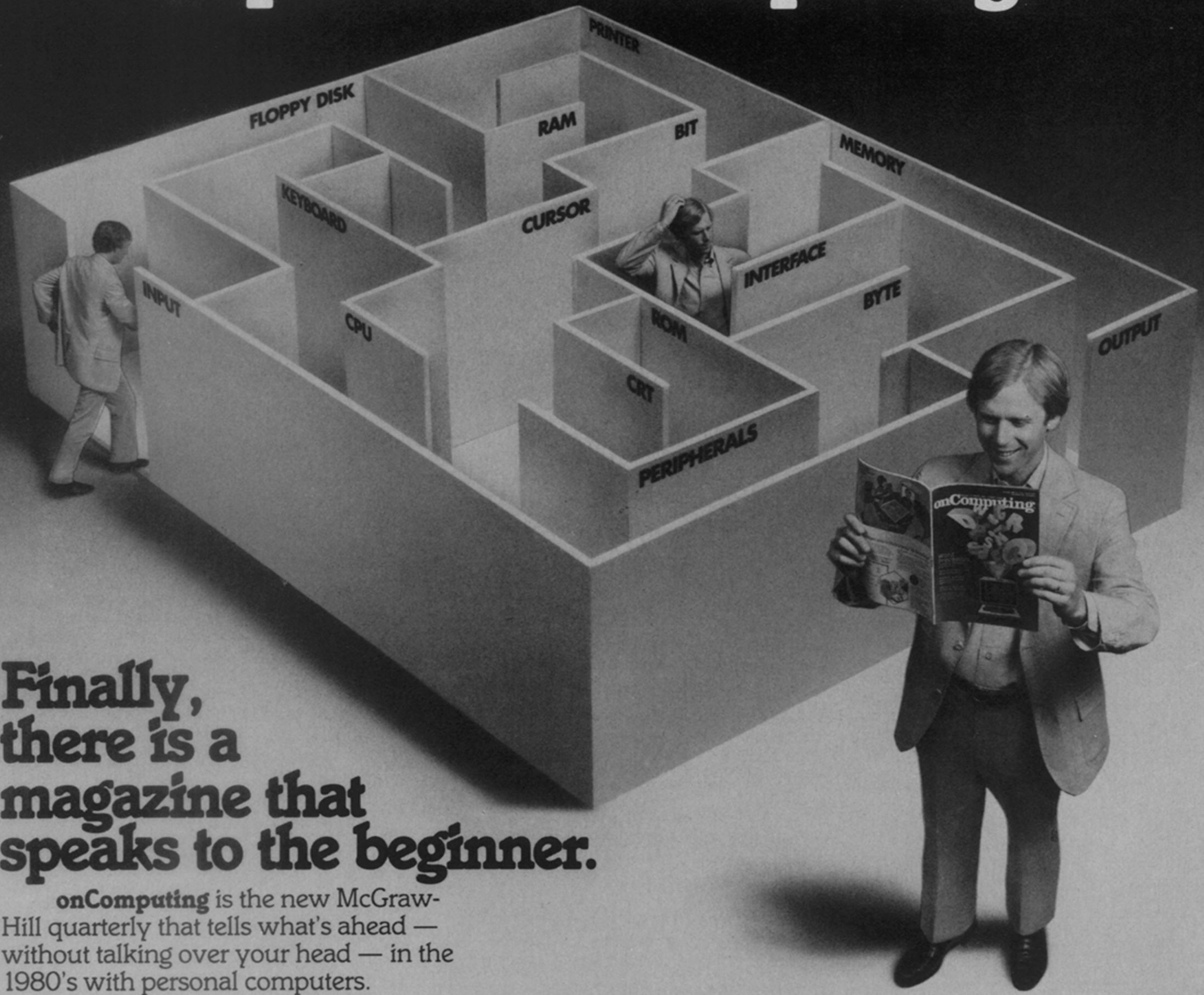

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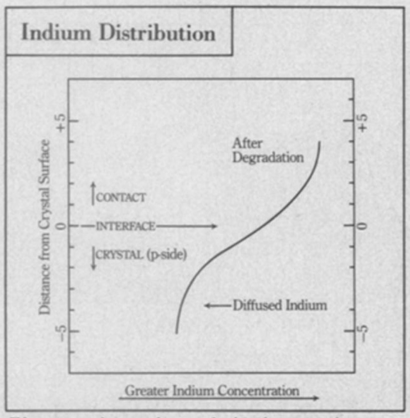
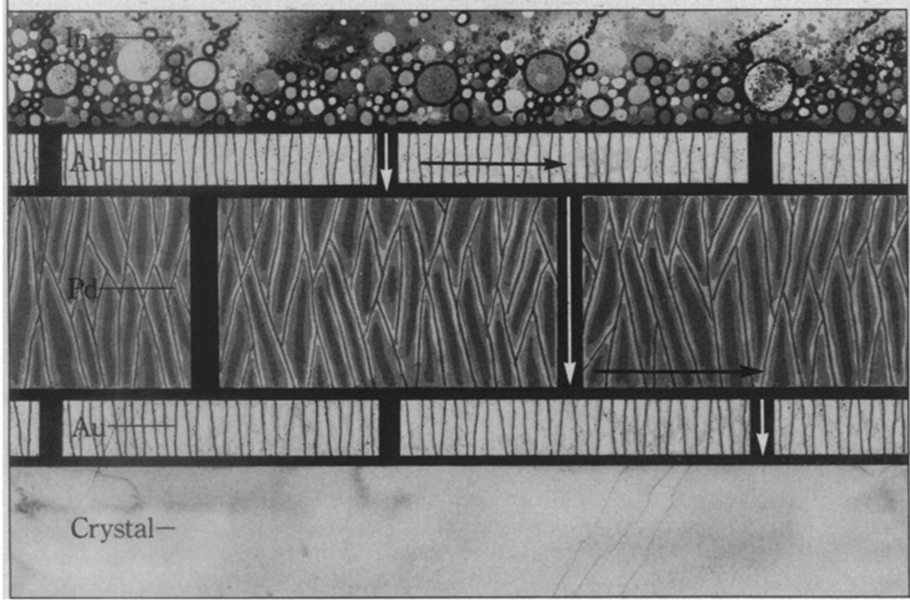
The Strategic Misalignment

Tunable semiconductor lasers can now measure specific gases in automotive exhaust with 25-millisecond response time. A successful strategy for improving laser reliability developed at the General Motors Research Laboratories makes this and other new spectroscopy capabilities practical realities.



Electron microprobe analysis of a crystal-contact interface, indicating indium penetration into the PbSnTe crystal.

Diagram of hypothetical indium diffusion paths for a three-layer contact structure of Au-Pd-Au.



THE ACHIEVEMENT of long lifetime and frequency stability makes the lead-tin-telluride diode laser a practical infrared spectrometer. Earlier innovations brought to this laser the characteristics of increased power, higher temperature operation, greater efficiency and wider tuning range.

Operating in the 5- to 10-micron range, the PbSnTe laser spectrometer can resolve the time-dependent emission of carbon monoxide, sulfuric acid vapor, methane and other species of interest in automotive exhaust. This permits measurement of transients in carbon monoxide to carbon dioxide gas conversion in a catalytic converter. This capability represents a significant advance over conventional spectroscopy instrumentation. The laser is also being tested by NASA for use in detecting the molecular species involved in chemical reactions in the stratosphere.

New knowledge of the process by which laser reliability is compromised has been revealed in fundamental studies conducted by Dr. Wayne Lo and his colleagues at General Motors. Dr. Lo's investigations have demonstrated that laser lifetime and stability are limited by the development of excessive electrical contact resistance. He has been able to stop increases in resistance by devising a multilayer ohmic contact consisting of different metal films. This configuration has extended laser operating lifetime to more than 1,000 hours and increased shelf-life to an estimated 25 years.

Slow degradation due to a gradual increase in contact resistance was observed in idle lasers stored at room temperature, but not in lasers maintained at a maximum temperature of 77 K, despite several hundred hours of continuous operation. These results suggested the temperature-dependent process of diffusion.

Degradation occurred primarily on the p-type side of the laser, where the contact consisted of a thin layer of gold followed by a layer of indium. Electron microprobe analyses revealed that indium, a semiconductor donor, was diffusing through the gold layer into the crystal, apparently causing a reduction in hole carrier concentration near the p-surface. This effect was counteracted to a great degree by sandwiching a thin layer of platinum between the layers of indium and gold. Laser reliability reached a full year.

When degradation was still observed, although to a reduced extent, Dr. Lo advanced the hypothesis that diffusion and transport were taking place along grain boundaries in the polycrystalline contact layers. He proposed replacing the Pt-Au barrier with a three-layer structure. Since palladium film structures have fewer grain boundaries than those of platinum, providing fewer leakage paths for the indium, Pd was tested in place of Pt.

DIODE LASERS composed of $Pb_{0.86}Sn_{0.14}Te$ and fabricated with a variety of contacts were maintained at 60°C in order to accelerate aging, with periodic interruptions for testing. The results showed that a multilayer structure of In-Au-Pd-Au, in which the grain boundaries tend to be misaligned, provides maximal reduction of indium penetration, confirming Dr. Lo's hypothesis.

The misaligned boundaries force diffusion to take place laterally, which slows transport into the crystal. The additional layer slows the process even further.

Solving the contact problem represents the culmination of efforts that began at General Motors with the development of an "ingot-nucleation" vapor transport method for growing crystals. The resulting crystals are of high purity, with a dislocation density of less than 1000 cm^{-2}. Lasers made from these crystals incorporate a low temperature cadmium-diffused p-n junction. This process, invented by Dr. Lo, increases the laser's output to five milliwatts.

A tuning range of 500 cm^{-1} and pulsed operating temperatures of up to 140 K are achieved by a two-step annealing process. This technique induces a graded carrier concentration that increases infrared light confinement in the laser structure, thus reducing losses and increasing output.

"These innovations," says Dr. Lo, "combine to produce a laser that allows us to make measurements previously impossible."

THE MAN BEHIND THE WORK

Dr. Wayne Lo is a Senior Research Scientist in the Physics Department at the General Motors Research Laboratories.

Dr. Lo was born in Hupei, China. He did his undergraduate work at Cheng-Kung University in Taiwan. He received an M.S. from the University of Rhode Island and a Ph. D. in electrical engineering from Columbia University in 1972. His doctoral thesis concerned the characterization of deep-level states and carrier lifetimes in gallium arsenide light-emitting diodes.

Before undertaking graduate studies, Dr. Lo was instrumental in setting up the first American transistor production plant in Taiwan. In 1973, he joined General Motors, where he is currently in charge of semiconductor laser and spectroscopy research.